

MMBF5460LT1

JFET - General Purpose Transistor

P-Channel

Features

- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V_{DG}	40	Vdc
Reverse Gate-Source Voltage	V_{GSR}	40	Vdc
Forward Gate Current	I_{GF}	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

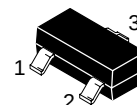
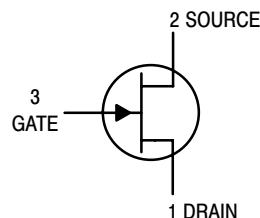
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.



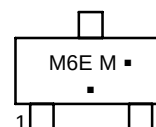
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SOT-23 (TO-236)
CASE 318
STYLE 10

MARKING DIAGRAM



M6E = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBF5460LT1	SOT-23	3,000 / Tape & Reel
MMBF5460LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBF5460LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Gate-Source Breakdown Voltage ($I_G = 10\ \mu\text{Adc}$, $V_{DS} = 0$)	$V_{(BR)GSS}$	40	–	–	Vdc
Gate Reverse Current ($V_{GS} = 20\ \text{Vdc}$, $V_{DS} = 0$) ($V_{GS} = 20\ \text{Vdc}$, $V_{DS} = 0$, $T_A = 100^\circ\text{C}$)	I_{GSS}	– –	– –	5.0 1.0	nAdc μAdc
Gate Source Cutoff Voltage ($V_{DS} = 15\ \text{Vdc}$, $I_D = 1.0\ \mu\text{Adc}$)	$V_{GS(off)}$	0.75	–	6.0	Vdc
Gate Source Voltage ($V_{DS} = 15\ \text{Vdc}$, $I_D = 0.1\ \text{mAdc}$)	V_{GS}	0.5	–	4.0	Vdc
ON CHARACTERISTICS					
Zero-Gate-Voltage Drain Current ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$)	I_{DSS}	–1.0	–	–5.0	mAdc
SMALL-SIGNAL CHARACTERISTICS					
Forward Transfer Admittance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{kHz}$)	$ Y_{fs} $	1000	–	4000	μmhos
Output Admittance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{kHz}$)	$ Y_{os} $	–	–	75	μmhos
Input Capacitance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{iss}	–	5.0	7.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15\ \text{Vdc}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{rss}	–	1.0	2.0	pF

**DRAIN CURRENT versus GATE
SOURCE VOLTAGE**

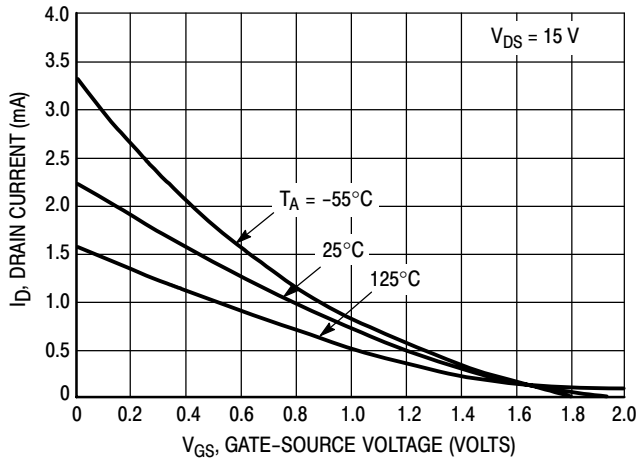


Figure 1. $V_{GS(off)} = 2.0$ Volts

**FORWARD TRANSFER ADMITTANCE
versus DRAIN CURRENT**

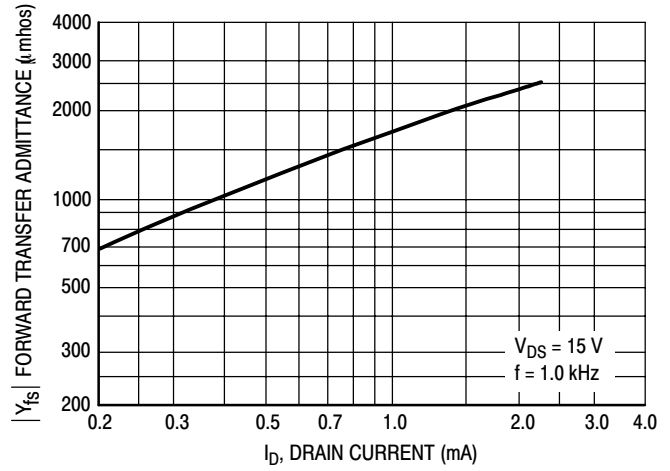


Figure 4. $V_{GS(off)} = 2.0$ Volts

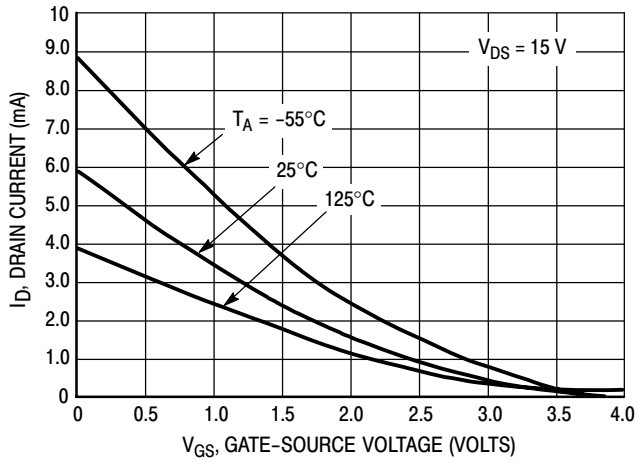


Figure 2. $V_{GS(off)} = 4.0$ Volts

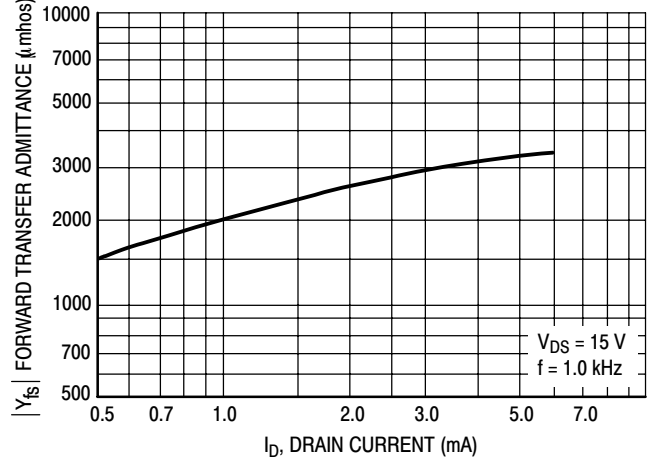


Figure 5. $V_{GS(off)} = 4.0$ Volts

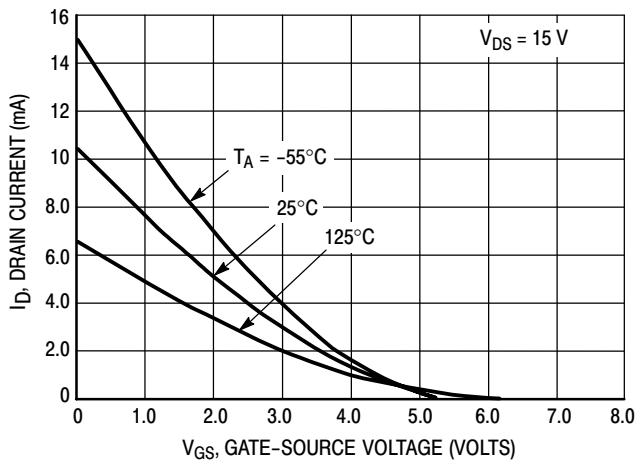


Figure 3. $V_{GS(off)} = 5.0$ Volts

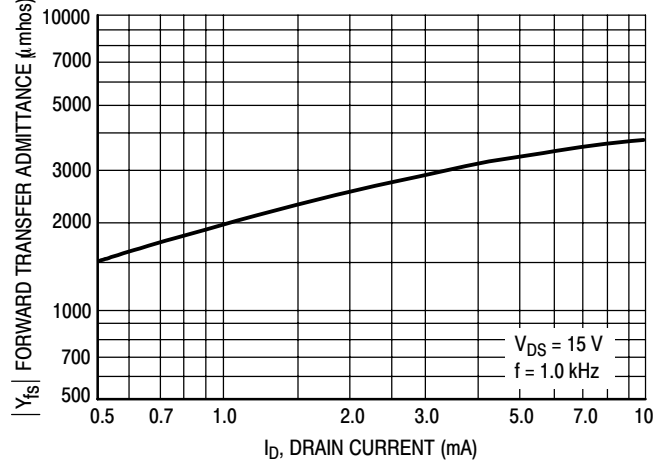


Figure 6. $V_{GS(off)} = 5.0$ Volts

MMBF5460LT1

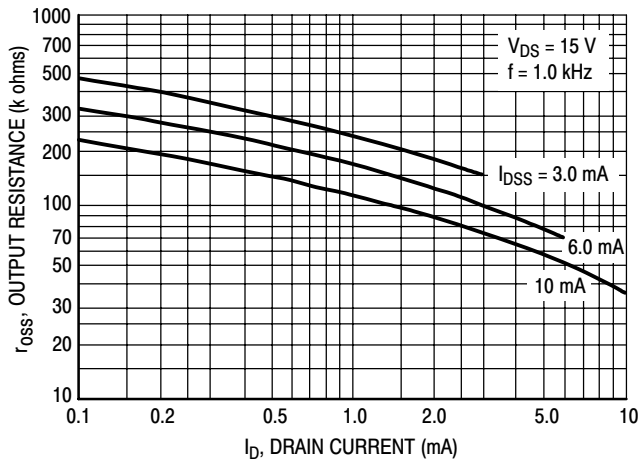


Figure 7. Output Resistance versus Drain Current

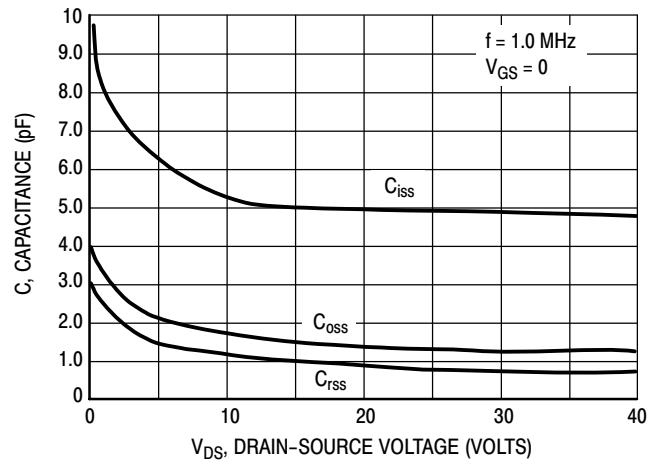


Figure 8. Capacitance versus Drain-Source Voltage

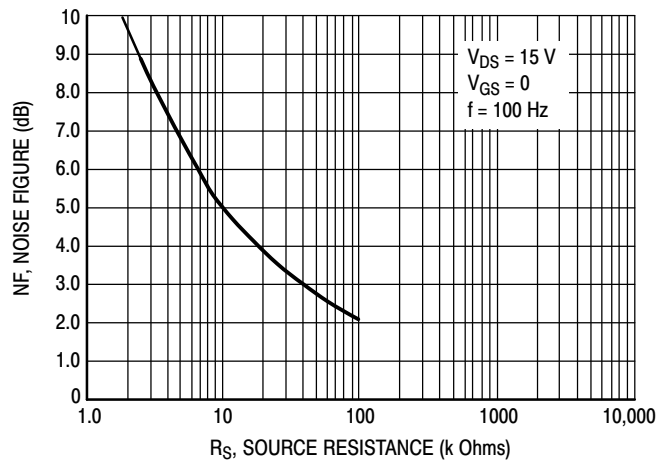
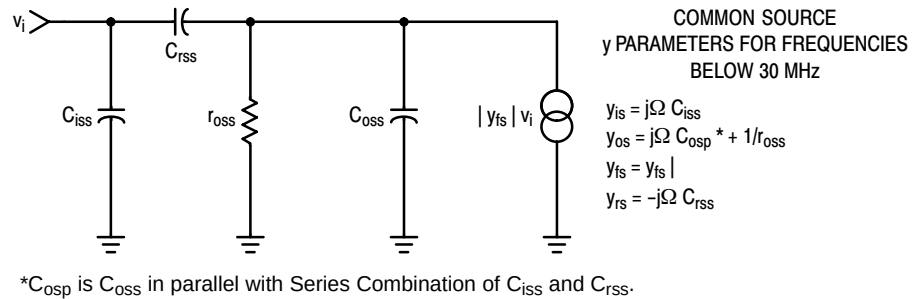


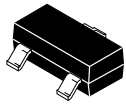
Figure 9. Noise Figure versus Source Resistance



NOTE:

1. Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

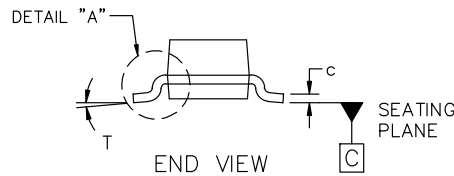
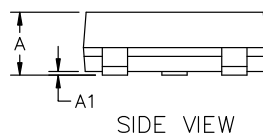
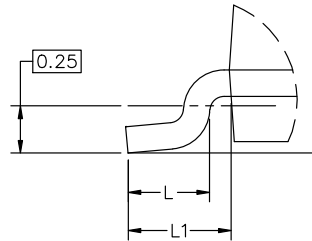
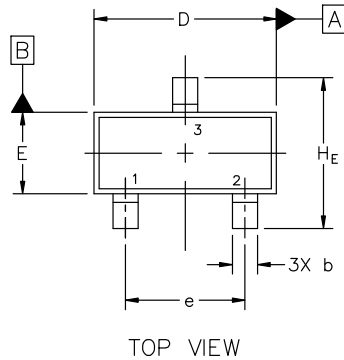
Figure 10. Equivalent Low Frequency Circuit



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

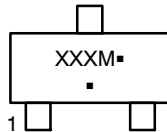
DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

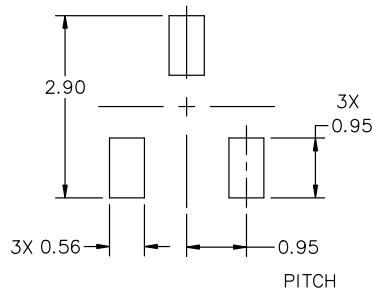
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*


XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.


RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLES ON PAGE 2

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DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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